

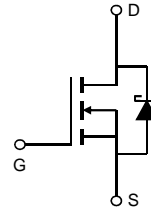
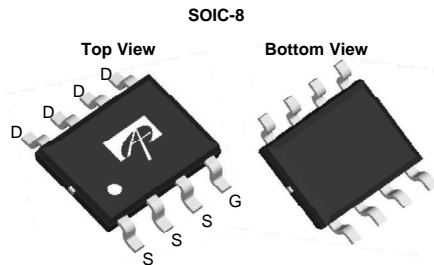
### General Description

SRFET™ AO4712 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent  $R_{DS(ON)}$ , and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

### Product Summary

$V_{DS}$	30V
$I_D$ (at $V_{GS}=10V$ )	13A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 11mΩ
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$ )	< 14mΩ

100% UIS Tested  
 100%  $R_g$  Tested



**SRFET™**  
 Soft Recovery MOSFET:  
 Integrated Schottky Diode

### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	±12	V
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	13
		$T_A=70^\circ\text{C}$	10
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	68	A
Avalanche Current <sup>C</sup>	$I_{AS}, I_{AR}$	15	A
Avalanche energy $L=0.1\text{mH}$ <sup>C</sup>	$E_{AS}, E_{AR}$	11	mJ
Power Dissipation <sup>B</sup>	$P_D$	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	32	40	°C/W
Maximum Junction-to-Ambient <sup>A, D</sup>		60	75	°C/W
Maximum Junction-to-Lead	$R_{\theta JL}$	17	24	°C/W

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =125°C			0.5 100	mA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.1	1.65	2.1	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	68			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =13A T <sub>J</sub> =125°C		9 13	11 16	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =11A		10.7	14	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =13A		80		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.4	0.7	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz	930	1170	1400	pF
C <sub>oss</sub>	Output Capacitance		90	128	170	pF
C <sub>riss</sub>	Reverse Transfer Capacitance		45	89	125	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.7	1.4	2.1	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =13A	16	20	24	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge		7	8.7	10.5	nC
Q <sub>gs</sub>	Gate Source Charge			3.2		nC
Q <sub>gd</sub>	Gate Drain Charge			3		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.2Ω, R <sub>GEN</sub> =3Ω		6		ns
t <sub>r</sub>	Turn-On Rise Time			2.4		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			23		ns
t <sub>f</sub>	Turn-Off Fall Time			4		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =13A, dI/dt=500A/μs	5.5	7	8.5	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =13A, dI/dt=500A/μs	5	6.5	8	nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

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**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

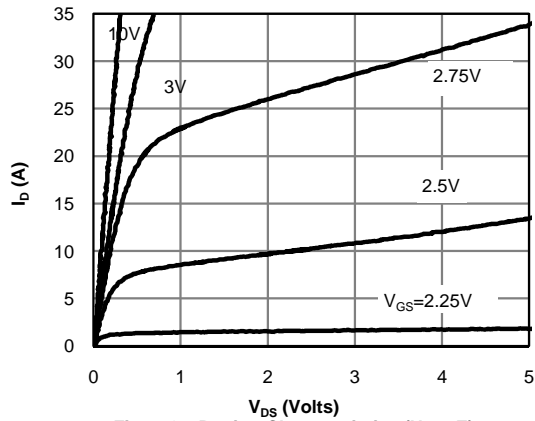


Fig 1: On-Region Characteristics (Note E)

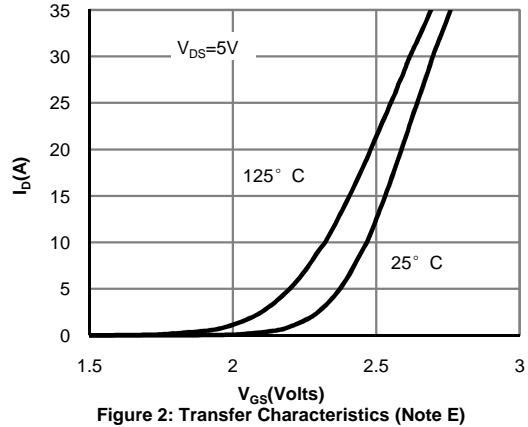


Figure 2: Transfer Characteristics (Note E)

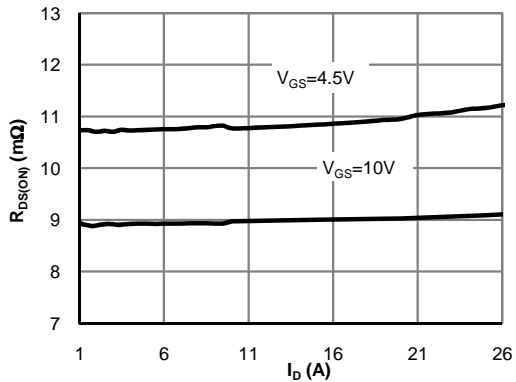


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

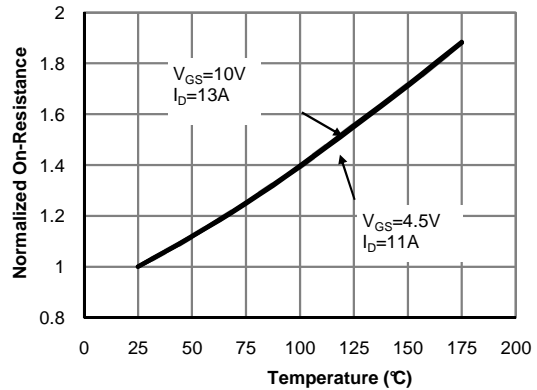


Figure 4: On-Resistance vs. Junction Temperature (Note E)

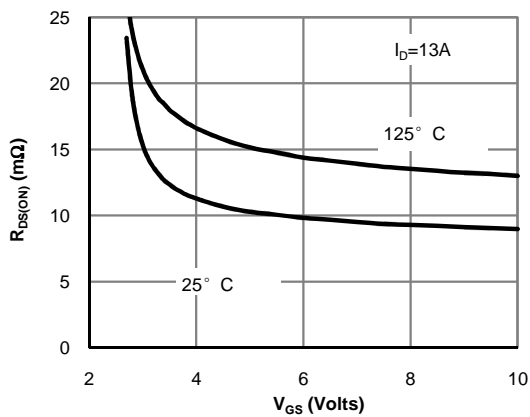


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

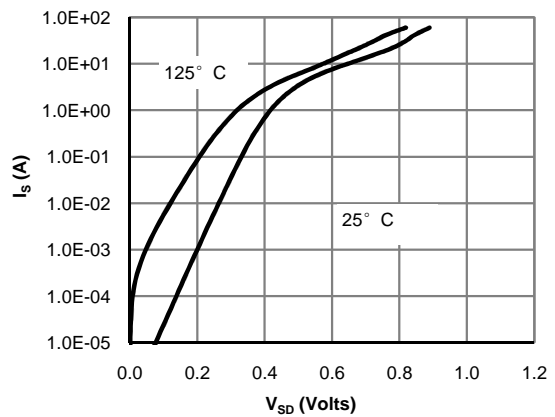


Figure 6: Body-Diode Characteristics (Note E)

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

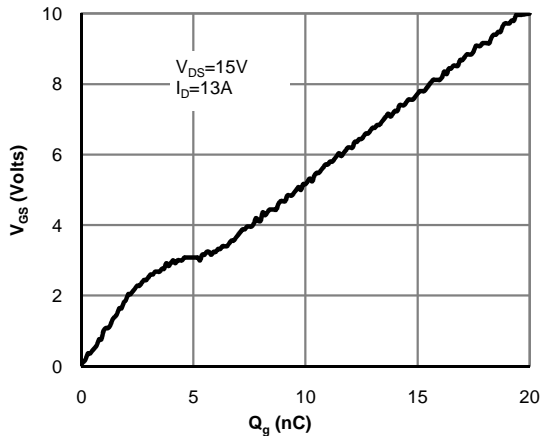


Figure 7: Gate-Charge Characteristics

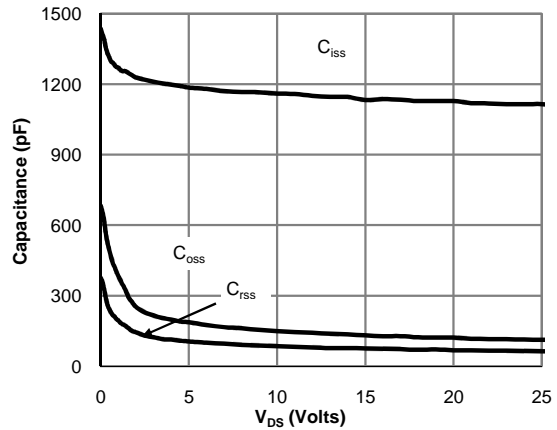


Figure 8: Capacitance Characteristics

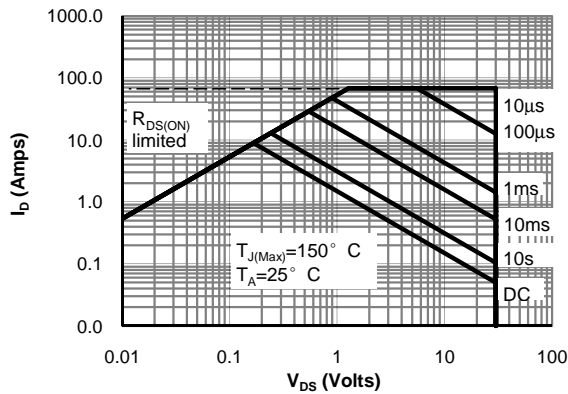


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

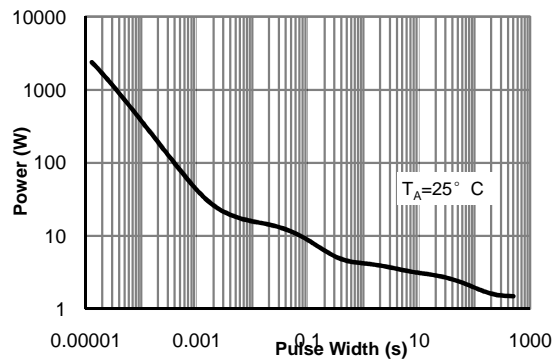


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

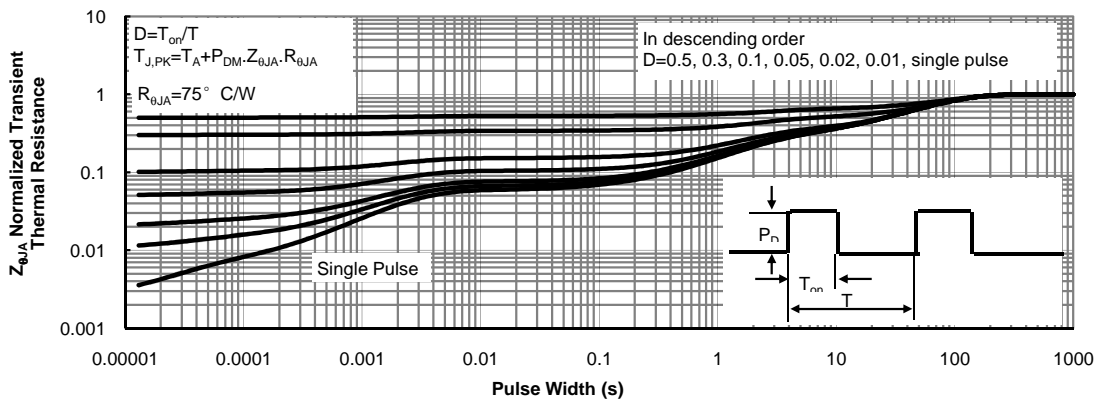


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

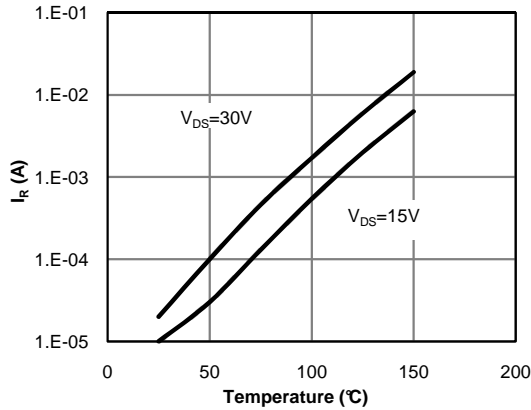


Figure 13: Diode Reverse Leakage Current vs. Junction Temperature

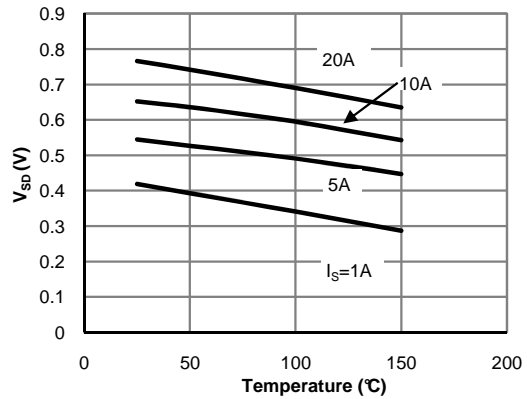


Figure 14: Diode Forward Voltage vs. Junction Temperature

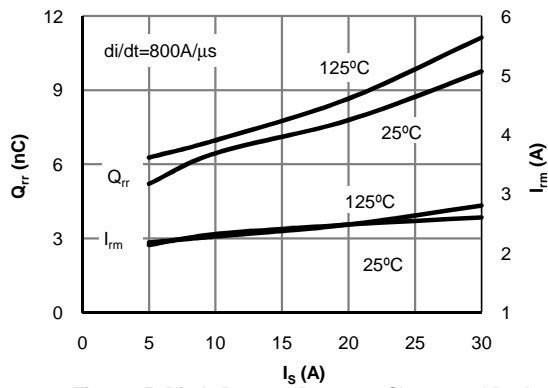


Figure 15: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

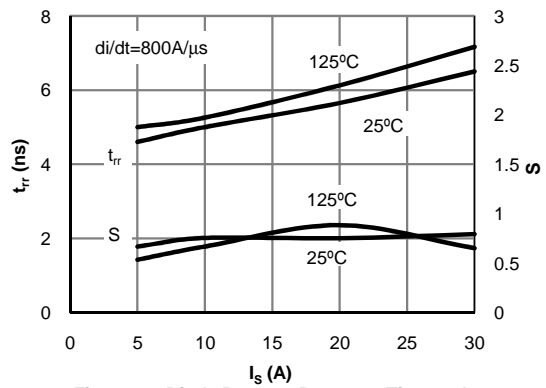


Figure 16: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current

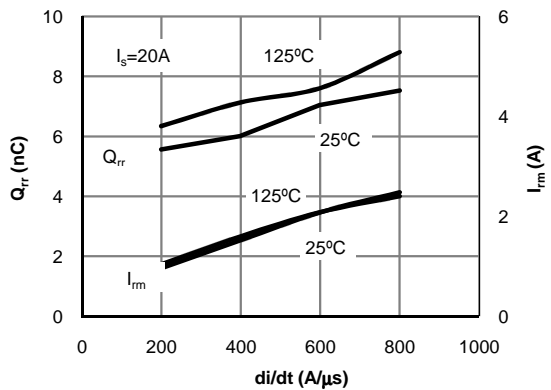


Figure 17: Diode Reverse Recovery Charge and Peak Current vs. di/dt

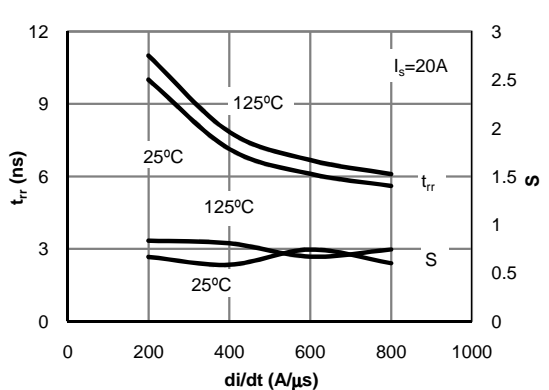


Figure 18: Diode Reverse Recovery Time and Softness Factor vs. di/dt

**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

